

# AM01A

# SILICON RECTIFIER DIODE

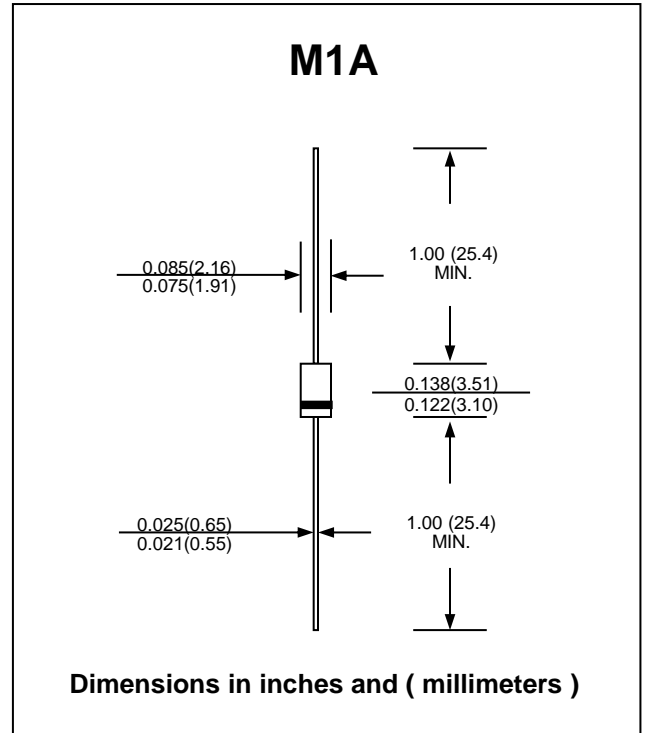
**PRV : 600 Volts**  
**Io : 1.0 Ampere**

### FEATURES :

- \* Glass passivated junction chip
- \* High current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* **Pb / RoHS Free**

### MECHANICAL DATA :

- \* Case : M1A Molded plastic
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.20 gram (approximately)



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	600	V
Maximum RMS Voltage	V <sub>RMS</sub>	420	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	600	V
Maximum Average Forward Current 0.375"(9.5mm) Lead Length Ta = 25 °C	I <sub>F(AV)</sub>	1.0	A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load	I <sub>FSM</sub>	35	A
Maximum Forward Voltage at I <sub>F</sub> = 1.0 A.	V <sub>F</sub>	0.98	V
Maximum DC Reverse Current Ta = 25 °C at rated DC Blocking Voltage Ta = 100 °C	I <sub>R</sub>	10	μA
	I <sub>R(H)</sub>	50	μA
Maximum Thermal Resistance (Junction to lead)	R <sub>θJL</sub>	22	°C/W
Junction Temperature Range	T <sub>J</sub>	- 40 to + 150	°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150	°C

## RATING AND CHARACTERISTIC CURVES ( AM01A )

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

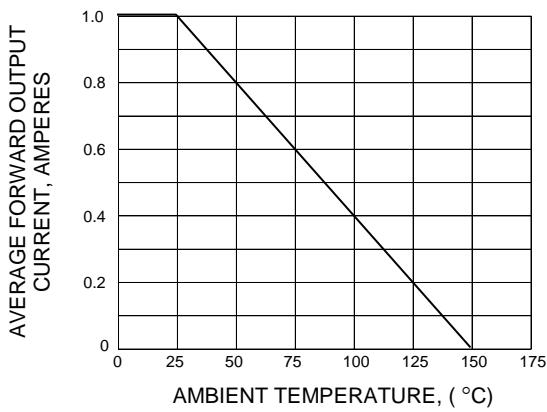


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

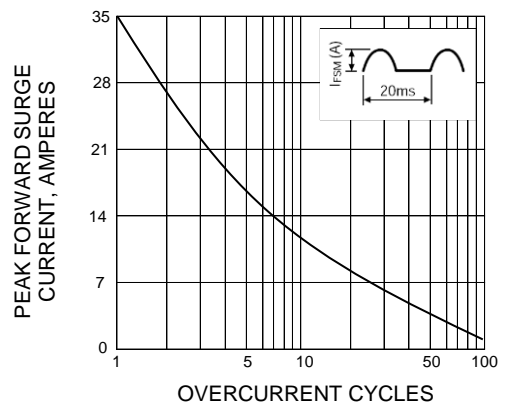


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

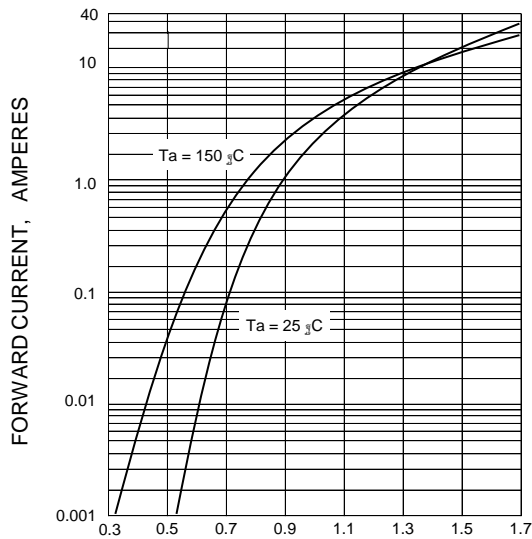


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

